

## IN THE CLAIMS

This listing of claims replaces all prior listings.

1-16. (canceled).

17. (currently amended) A method of fabrication of a semiconductor device, comprising the steps of:

die bonding of a plurality of semiconductor chips on a substrate;

forming a target mark in the substrate, the target mark corresponding to the semiconductor chips;

forming of a first insulation film on said substrate, wherein a top surface and at least a portion of side surfaces of said plurality of semiconductor chips are incrustated in said first insulation film;

forming a second insulation film directly on and contacting the first insulation film, the minimum height of a top surface of the second insulation film exceeding the maximum height of a top surface of the first insulation film;

grinding flat the second insulation film;

forming a third insulation film directly on and contacting the flatly ground second insulation film;

forming of a connection hole reaching a semiconductor chip of said plurality of semiconductor chips through said first insulation film, said second insulation film, and said third insulation film; and

forming of wiring on said third insulation film, wherein said wiring is connected to said semiconductor chip through said connection hole.

18. (previously presented) The method of fabrication of a semiconductor device according to claim 17, further comprising the steps of:

forming of an upper layer insulation film on said third insulation film, wherein said upper layer insulation film covers said wiring;

forming of a connection hole reaching said wiring, on said upper layer insulation film;  
and

forming of an electrode on said upper layer insulation film, wherein said electrode is connected to said wiring through said connection hole.

19. (previously presented) The method of fabrication of a semiconductor device according to claim 17, wherein said substrate is a silicon wafer.

20. (original) The method of fabrication of a semiconductor device according to claim 17, wherein

said die bonding of said plurality of semiconductor chips on said substrate comprises die bonding of each said semiconductor chips on said substrate, wherein each said semiconductor chip is set so as to float on an adhesive resin applied on said substrate.

21. (original) The method of fabrication of a semiconductor device according to claim 17, wherein

after said step of forming said wiring, said substrate is removed from said semiconductor chip and said insulation film.